

ASC500N1200MED

1200V, 3.2mΩ, Half-Bridge, Silicon Carbide MOSFET Module

Product Data Sheet

ASTC-3T03-222A A/0



爱仕特半导体

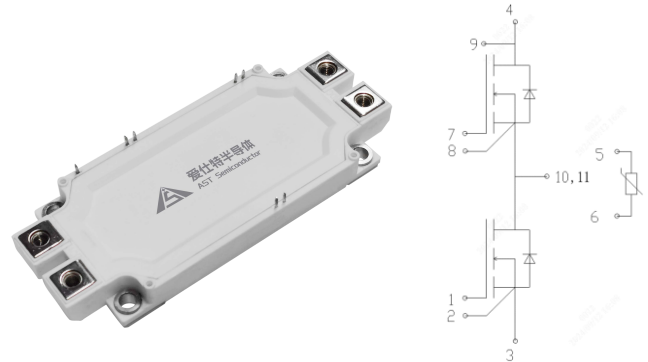
AST Semiconductor

General Description

The AST-MED module incorporates AST's 1200V Gen3 N-channel SiC MOSFET. NTC temperature sensor inside.

Features

- High Temperature, Humidity, and Bias Operation
- Ultra Low Loss
- High-Frequency Operation
- Zero Turn-off Tail Current from MOSFET
- Normally-off, Fail-Safe Device Operation
- Copper Baseplate and Silicon Nitride Insulator



Applications

- High Power Converters
- Motor Drives
- Servo Drives
- UPS Systems
- Wind Turbines

Ordering Informations

Order Number	ASC500N1200MED
Marking	ASC500N1200MED
Package Type	MED

Key Parameters

Symbol	Parameter	Values			Unit	Test Conditions
Absolute maximum rating						
V _{DS}	Drain-Source Voltage	1200			V	T _c =25°C
I _D	Drain Current (continuous)	360			A	T _c =65°C; V _{GS} =18V
T _J ; MAX	Junction Temperature	175			°C	
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics						
R _{DS(on)}	Static Drain-Source on Resistance	-	3.2	4.4	mΩ	V _{GS} =18V; I _D =300A; T _c =25°C
Dynamic characteristics						
Q _G	Total Gate Charge	-	1190	-	nC	V _{DD} =800V; V _{GS} =-5/+18V; I _D =300A; T _c =25°C
Q _{GD}	Gate-Drain Charge	-	392	-		
Source-drain diode						
Q _{RR}	Reverse Recovery Charge	-	3.1	-	μC	V _{GS} =-5/+18V; I _F =300A; V _R =900V; Load=100μH; R _{G(ext)} =5Ω; T _J =25°C

Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	1200	V
V_{GS}	Gate-Source Voltage (dynamic)	-10/+22	V
I_D	Drain Current (continuous; $T_c=65^\circ\text{C}$; $V_{GS}=18\text{V}$)	360	A
I_{DM}	Drain Current (pulsed)	720	A
T_{op} ; T_{stg}	Operating and Storage Temperature Range	-40 to +175	$^\circ\text{C}$
T_J	Junction Temperature	175	$^\circ\text{C}$
L_{Stray}	Stray Inductance	20	nH
V_{isol}	Isolation Test Voltage (DC; 2mA; $t=10\text{s}$)	4.2	kV
$R_{th Jh}$	Thermal Resistance, Junction-to-Heatsink	0.12	$^\circ\text{C/W}$

MOSFET Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics (at $T_c=25^\circ\text{C}$ unless otherwise specified)						
BV_{DS}	Drain-Source Breakdown Voltage	1200	-	-	V	$V_{GS}=0\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	-	-	50	μA	$V_{DS}=1200\text{V}$; $V_{GS}=0\text{V}$
I_{GSS}	Gate-Body Leakage Current	-	-	2.5	μA	$V_{GS}=-10/+20\text{V}$; $V_{DS}=0\text{V}$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.8	4.0	V	$V_{DS}=V_{GS}$; $I_D=50\text{mA}$
$R_{DS(on)}$	Static Drain-Source on Resistance	-	3.2	4.4	$\text{m}\Omega$	$V_{GS}=18\text{V}$; $I_D=300\text{A}$
$V_{GS(on)}$	Recommended Turn-on Voltage	-	18	-	V	Static
$V_{GS(off)}$	Recommended Turn-off Voltage	-	-5	-		
R_G	Gate Resistance	-	0.6	-	Ω	$V_{AC}=25\text{mV}$; $f=1\text{MHz}$
Dynamic characteristics (at $T_c=25^\circ\text{C}$ unless otherwise specified)						
C_{iss}	Input Capacitance	-	34.4	-	nF	$V_{DS}=1000\text{V}$; $f=100\text{kHz}$; $V_{AC}=25\text{mV}$
C_{oss}	Output Capacitance	-	1.44	-		
C_{rss}	Reverse Transfer Capacitance	-	65	-	pF	
E_{on}	Turn-on Energy	-	25.7	-	mJ	$V_{DS}=900\text{V}$; $V_{GS}=-5/+18\text{V}$; $I_D=300\text{A}$; $R_{G(ext)}=5\Omega$; Load=100 μH
E_{off}	Turn-off Energy	-	15.8	-		
Q_{GS}	Gate-Source Charge	-	384	-	nC	$V_{DD}=800\text{V}$; $V_{GS}=-5/+18\text{V}$; $I_D=300\text{A}$
Q_{GD}	Gate-Drain Charge	-	392	-		
Q_G	Total Gate Charge	-	1190	-		
$t_{d(on)}$	Turn-on Delay Time	-	105	-	ns	$V_{DD}=900\text{V}$; $V_{GS}=-5/+18\text{V}$; $I_D=300\text{A}$; $R_{G(ext)}=5\Omega$; Load=100 μH
t_r	Rise Time	-	82	-		
$t_{d(off)}$	Turn-off Delay Time	-	343	-		
t_f	Fall Time	-	62	-		



Body Diode Characteristics (at $T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V_{FSD}	Forward Voltage	-	3.5	6	V	$V_{GS}=0\text{V}$; $I_F=250\text{A}$
I_S	Continuous Diode Forward Current	-	250	-	A	$V_{GS}=0\text{V}$; $T_C=25^{\circ}\text{C}$
t_{RR}	Reverse Recovery Time	-	41	-	ns	$V_{GS}=-5/+18\text{V}$; $I_F=300\text{A}$; $V_R=900\text{V}$; $R_{G(ext)}=5\Omega$; Load= $100\mu\text{H}$
Q_{RR}	Reverse Recovery Charge	-	3.1	-	μC	
I_{RRM}	Peak Reverse Recovery Current	-	77	-	A	

Module Physical Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
W	Weight	-	350	-	g	-
M	Terminal Connection Torque, Screw M6 Mounting Torque, Screw M5	3.0	-	6.0	Nm	-
-	Clearance Distance	-	10.0	-	mm	Terminal to Terminal
		-	12.5	-		Terminal to Baseplate
-	Creepage Distance	-	11.5	-	mm	Terminal to Terminal
		-	14.7	-		Terminal to Baseplate

NTC Thermistor Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
R_{25}	Rated Resistance	-	5.00	-	k Ω	$T_{NTC}=25^{\circ}\text{C}$
$\Delta R/R$	Deviation of R_{100}	-5	-	5	%	$T_{NTC}=100^{\circ}\text{C}$; $R_{100}=493.3\Omega$
$B_{25/50}$	Beta Value for 25°C to 50°C	-	3375	-	K	$R_2=R_{25} \exp[B_{25/50}(1/T_2 - 1/(298.15\text{K}))]$
$B_{25/80}$	Beta Value for 25°C to 80°C	-	3414	-	K	$R_2=R_{25} \exp[B_{25/80}(1/T_2 - 1/(298.15\text{K}))]$
$B_{25/100}$	Beta Value for 25°C to 100°C	-	3436	-	K	$R_2=R_{25} \exp[B_{25/100}(1/T_2 - 1/(298.15\text{K}))]$

Typical Performance

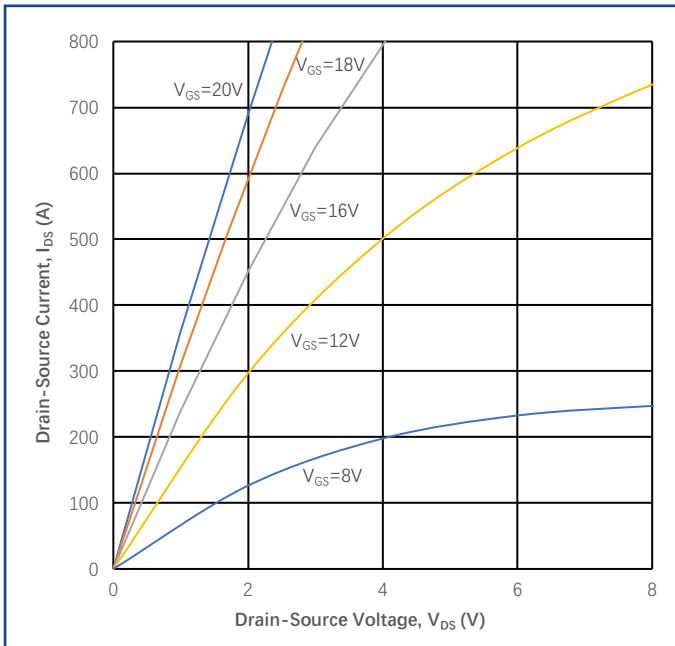


Figure 1
Output Characteristics ($T_J = 25^\circ\text{C}$)

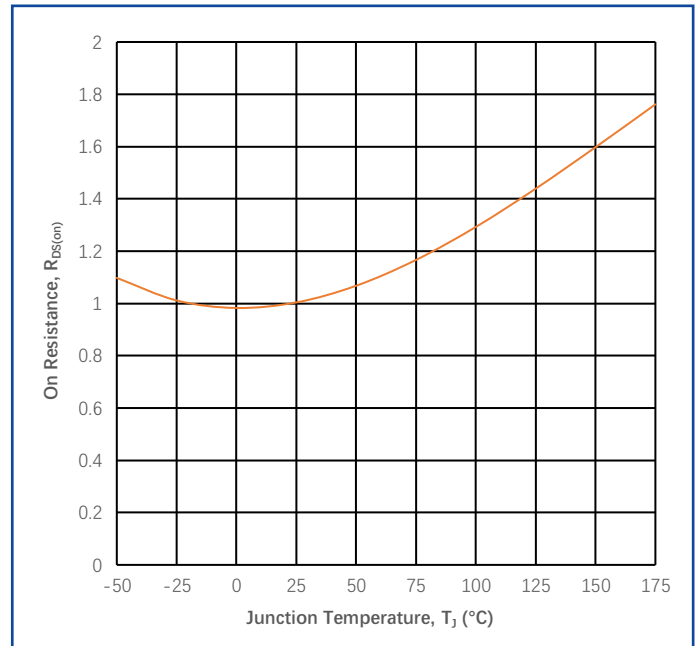


Figure 2
Normalized On-Resistance vs. Temperature

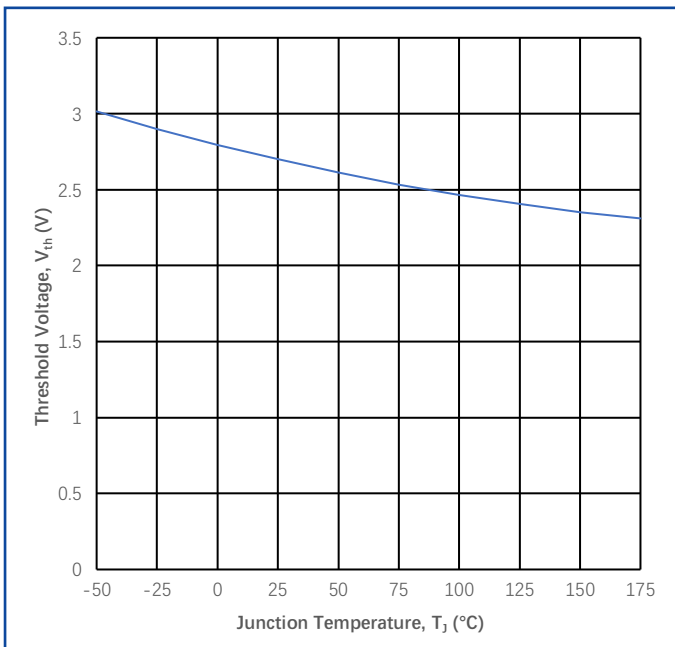


Figure 3
Threshold Voltage vs. Temperature

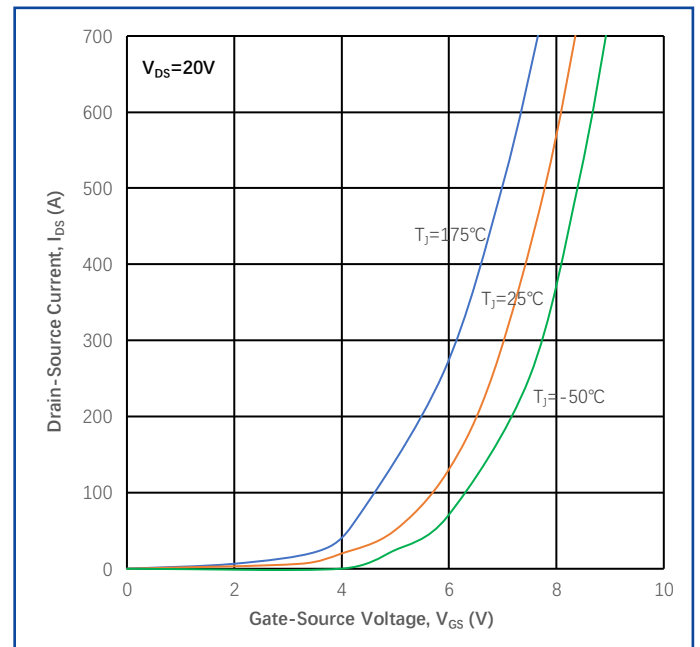


Figure 4
Transfer Characteristic for Various T_J

Typical Performance

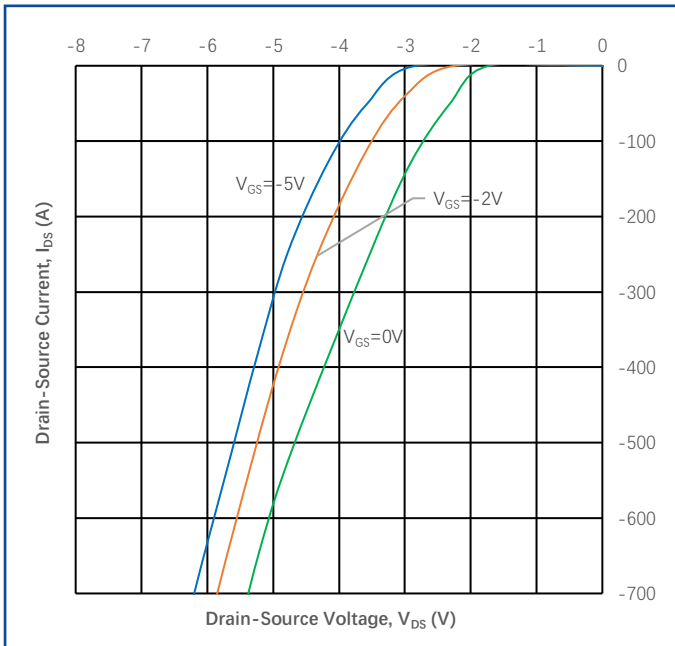


Figure 5
Diode Characteristic at 25°C

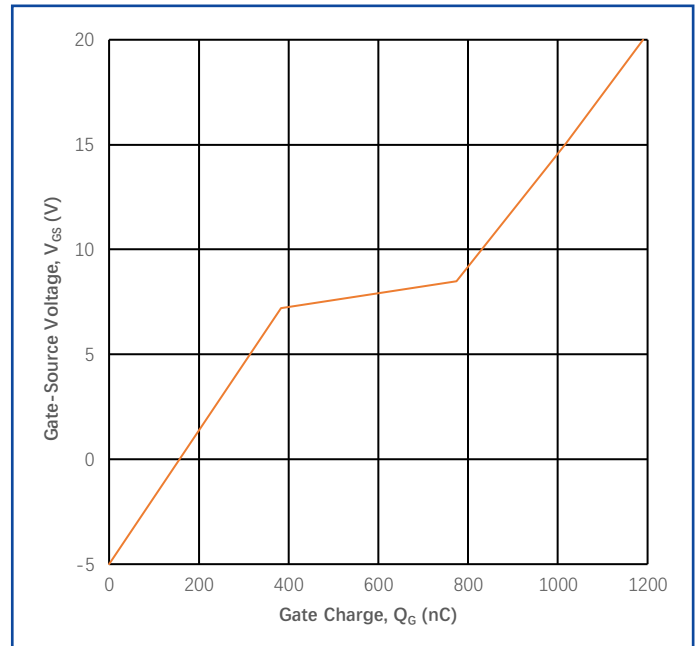


Figure 6
Typical Gate Charge Characteristics

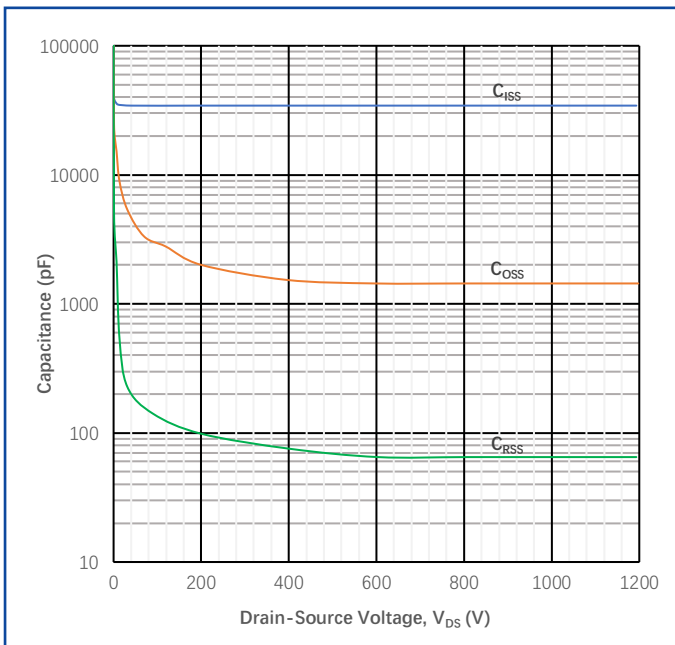


Figure 7
Typical Capacitances vs. Drain-Source Voltage

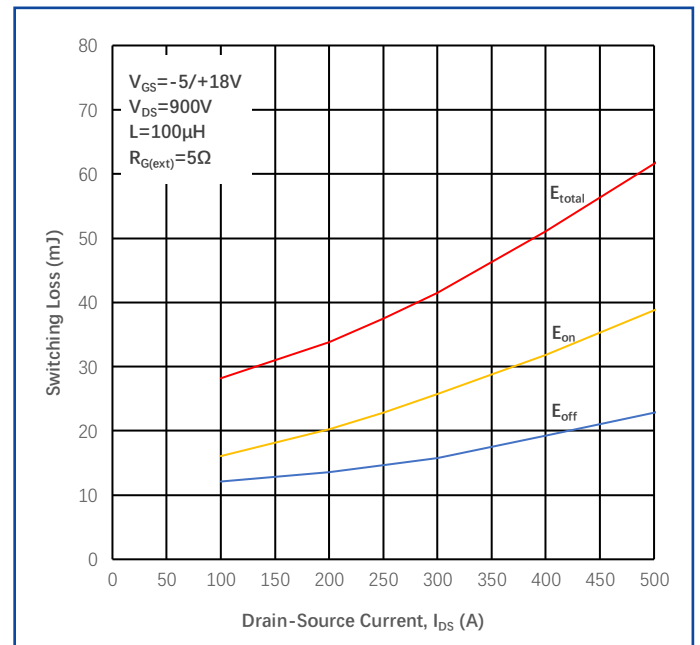


Figure 8
Inductive Switching Energy vs. Drain Current

Typical Performance

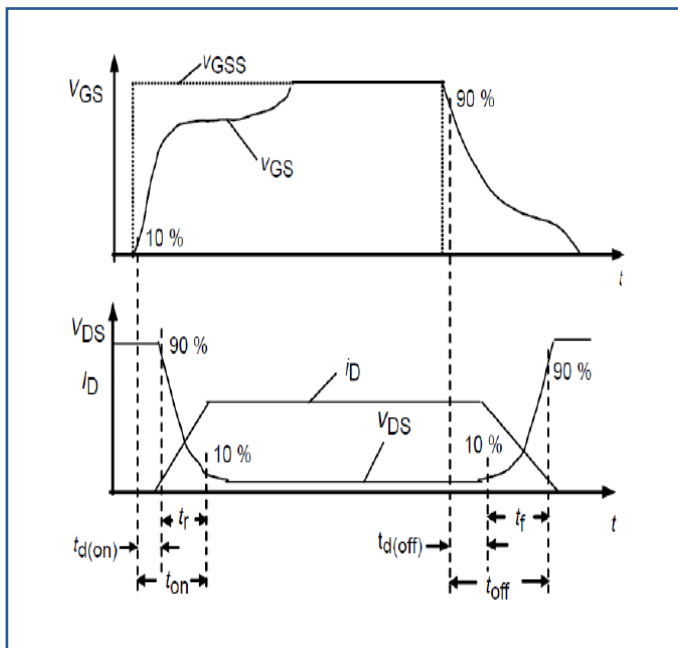


Figure 9

Switching Time Description

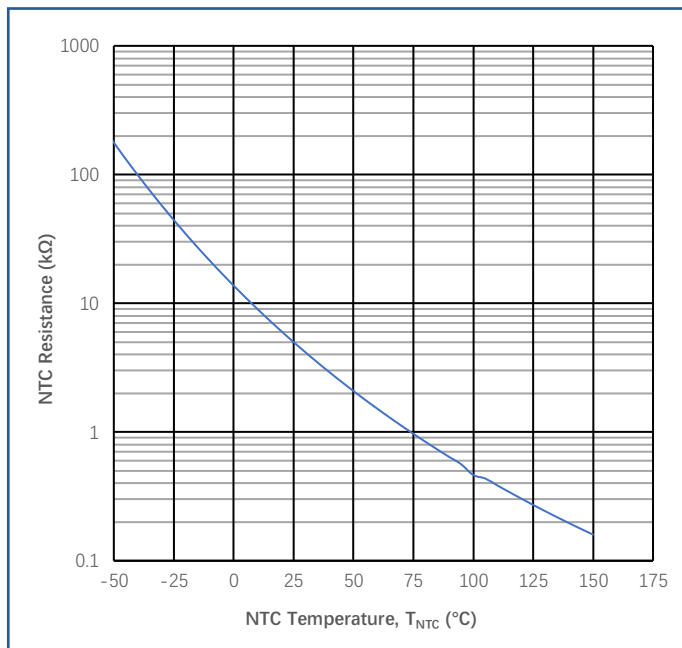
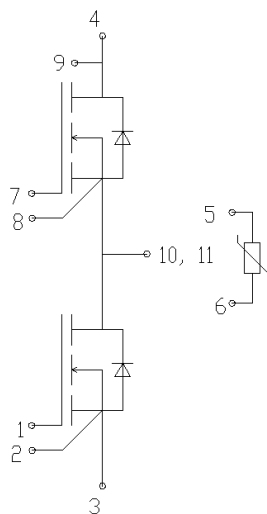


Figure 10

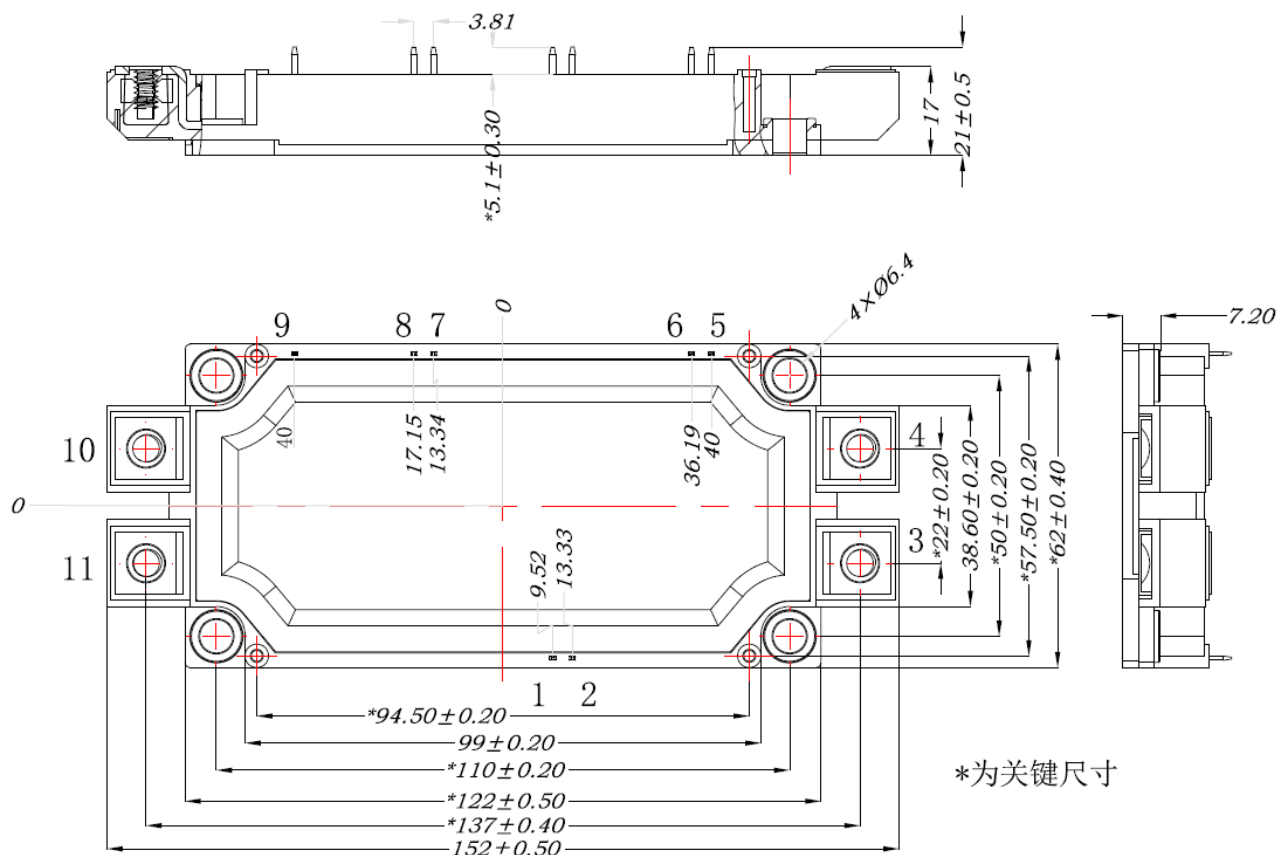
NTC-Temperature Characteristic (typical)

Circuit Diagram Headline



Package Dimensions (mm)

Package Type: MED



未标注线性公差按 GB/1804-2000c 级执行	公差分段	0.5-3	3-6	6-30	30-120	120-400
	c 级	±0.2	±0.3	±0.5	±0.8	±1.2

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